

β -Silyl Carbonyl Groups as New Photodegradation Units in Poly(butadienes)

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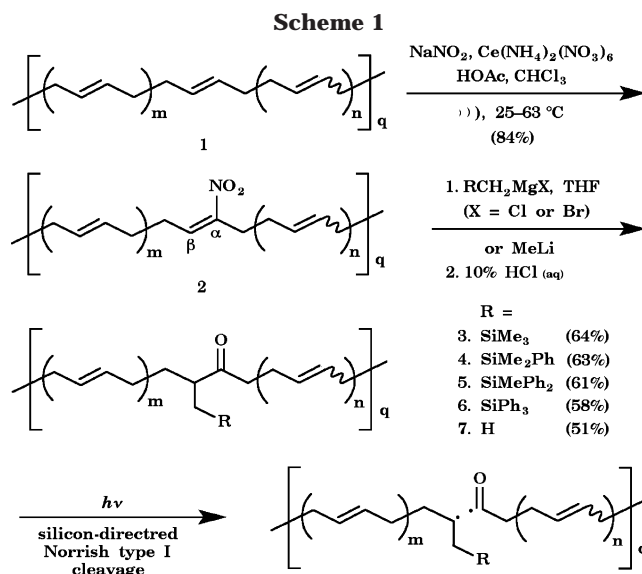
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The invention of new methods for the production of photodegradable polymers¹ is at the high desire of modern industry and environmental protection.² We planned to apply the silicon-promoted Norrish type I cleavage in the development of new photodegradable polymers. Our design was based on a previous report that photolysis rates of ketones by UV light are increased by placement of a Me₃Si group at the β -position.³ Herein we disclose our new findings that incorporation of a β -(triorgano)silyl ketonic unit ((-CH-(CH₂SiR₃)C(=O)-) into poly(butadienes) allowed dramatic improvement on their photodegradability.

Poly(butadienes) **1** represent a broad class of diene rubbers, which play a prominent role in the industries of photolithography, microelectronics, and mechanical industry.⁴ Several modified poly(butadiene) derivatives have been applied as positive-working photoresist compositions.⁵ To incorporate β -silyl ketonic units in poly(butadienes) for increasing their photodegradability, we applied two reactions in sequence (see Scheme 1). First, we treated commercially available poly(butadienes) (**1**, 902 mg, M_w 1.61×10^4 and M_n 1.51×10^4) with sodium nitrite (2.30 g), ceric ammonium nitrate (3.66 g), and acetic acid (2.29 mL) in a sealed bottle under sonication at 600 W and 23–63 °C.⁶ After 5.0 h, the desired nitroalkene-containing poly(butadienes) **2** were obtained in 84% yield upon neutralization of the reaction mixture with Na₂CO₃(s) and precipitation from hexanes. Polymers **2** exhibited IR absorptions at 1550 and 1346 cm⁻¹ resulting from the conjugated nitro group, a broad ¹H NMR signal around δ 7.03–7.24 ppm for the HC=CN proton, and two ¹³C NMR signals at δ 151.07 and 136.32 ppm for the α and β carbons, respectively, in HC β =C α -NO₂.⁷

Second, we incorporated the Me₃SiCH₂- and the ketonic groups into **2** (159 mg) by using Me₃SiCH₂MgCl (0.985 M in ether, 740 μ L) in THF (10 mL) at 0 °C for 1.5 h. The resultant solution was acidified to pH \sim 2.0 with 10% aqueous HCl, and stirring was continued at room temperature for 7.0 h. After the silicon-promoted Nef reaction was complete,⁸ we purified the precipitates with hexanes to give polymers **3** in 64% yield as a reddish-brown viscoelastomer. The presence of a carbonyl group in **3** is indicated by an IR absorption at 1724 cm⁻¹ and a ¹³C NMR signal at δ 203.45 ppm. Furthermore, an IR absorption at 1250 cm⁻¹ and a broad ¹H NMR absorption around δ -0.21 to 0.17 ppm demonstrate the successful introduction of an Si(CH₃)₃ group.



Various silyl groups may exhibit promoted effect in different degrees on the Norrish type I photocleavage and, thus, the photodegradability of new silyl ketone-containing polymers. Accordingly, we synthesized a series of silyl ketone-containing poly(butadienes) **4–6** in 58–63% yields by adding the corresponding silylmethyl Grignard reagents⁹ (R¹R²R³SiCH₂MgCl; R¹, R², R³ = Me or Ph) to poly(nitrobutadienes) **2** in THF at 0 °C (Scheme 1). The solutions were acidified to pH \sim 2.0 with 10% aqueous HCl at room temperature. Poly(nitrobutadienes) **2** exhibited IR absorptions at 1550 and 1346 cm⁻¹ for the conjugated nitro group. After a β -silyl ketonic unit was inserted to give silyl ketone-containing polymers **3–6**, an absorption showed up at \sim 1255 cm⁻¹ for Si–Me or at \sim 1115 cm⁻¹ for Si–Ph.¹⁰

To investigate photodegradation efficiency resulting from the β -(triorgano)silyl ketonic units in poly(butadienes), we carried out photolysis of several polymers in THF (0.26% w/v) at room temperature. A 450 W medium-pressure mercury UV lamp and a Pyrex filter ($\lambda \geq 300$ nm) were used to provide light with intensity 26.5 ± 0.8 mW/cm². The polymers included poly(butadienes) **1** as the reference, **3** (M_w 1.74×10^4 and M_n 1.36×10^4) with 4.4 mol % of the β -trimethylsilyl ketonic unit, **4** (M_w 1.41×10^4 and M_n 1.06×10^4) with 6.3 mol % of the β -(dimethylphenyl)silyl ketonic unit, **5** (M_w 1.92×10^4 and M_n 1.43×10^4) with 6.2 mol % of the β -(diphenylmethyl)silyl ketonic unit, and **6** (M_w 1.48×10^4 and M_n 1.14×10^4) with 9.0 mol % of the β -(triphenyl)silyl ketonic unit as well as polymers **7** (M_w 1.47×10^4 and M_n 1.03×10^4). Polymers **7**, containing 3.7 mol % of β -norsilyl ketonic unit, were prepared from **2** and MeLi (cf. Me₃SiCH₂MgBr for **3**) by the same procedure for **2** \rightarrow **3**.

We determined the average numbers of bond broken (i.e., [(M_n)₀/ M_n] - 1) by GPC at different time intervals for polymers **1** and **3–7** (see Figure 1). Poly(butadienes) **1** were almost completely resistant to photolysis; in contrast, ketone-containing polymers **3–7** exhibited strong photodegradability. From the average numbers of bond broken and their degradable units, we obtained the ratios $<1.0\%$ for **1**, 20.3% for **3**, 14.9% for **4**, 17.1% for **5**, 13.7% for **6**, and 7.25% for **7** (see Table 1). These

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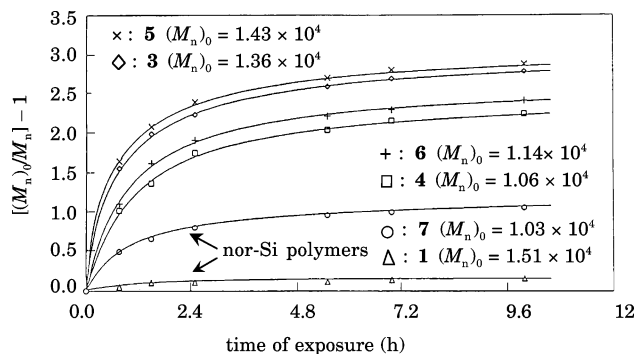


Figure 1. Average number of bond broken (i.e., $[(M_n)_0/M_n] - 1$) as a function of irradiation time by UV light with $\lambda \geq 300$ nm and intensity 26.5 ± 0.8 mW/cm² at room temperature.

Table 1. Results of Photodegradation from β -(Triorgano)silyl Ketonic Units in Poly(butadienes) after Irradiation for 2.0 h

polymer	av no. of bond broken ^a	degradable unit ^b	efficiency (%) ^c
3	2.07	10.2	20.3
4	1.55	10.4	14.9
5	2.22	13.0	17.1
6	1.75	12.8	13.7
7	0.642	8.85	7.25

^a $[(M_n)_0/M_n] - 1$. ^b Calculated from $(M_n/M_m) \times (\text{mol \% of Si-containing unit})$. The term M_m represents the average molecular weight of monomers. The mole percentage of Si-containing or methyl unit in polymers was determined by ¹H NMR spectrometry. ^c Reflected by (the average number of bond broken)/(the degradable unit).

values indicate their efficiency of degradation. The strength of influence for a silyl group at the β position of a carbonyl group follows the order $\text{Me}_3\text{Si} > \text{MePh}_2\text{Si} > \text{Me}_2\text{PhSi} > \text{Ph}_3\text{Si} > \text{H}$.

We found that the β -trimethylsilyl ketonic moiety displayed the most appealing photodegradation effect. Degradability was much higher for polymers **3** than the parent poly(butadienes) **1**. The effect is believed to come from the stabilization ability of a silyl group toward β carboradical through " σ - π hyperconjugation"¹¹ and, perhaps, " p - d homoconjugation".¹² Both the electronic and the steric effects resulting from the substituents on the silicon atom may affect its stabilization ability.¹³ The net effect of a silyl group may come from the combination of both.

In conclusion, a new method was developed to make poly(butadienes) photodegradable and applicable as a positive photoresist. It involves incorporation of a β -(triorgano)silyl ketonic unit $[-\text{CH}(\text{CH}_2\text{SiR}_3)\text{C}(=\text{O})-]$ through nitration, Michael addition, and Nef reactions. The resultant poly[but-2-ene-*co*-3-(triorganosilyl) methylbutan-2-ones] possessed thermal stability and desired photodegradability. The outcomes will broaden the usage of polydiene rubbers.

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Supporting Information Available: Synthetic procedures and spectroscopic characterization of all new compounds. This material is available free of charge via the Internet at <http://pubs.acs.org>.

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